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Authors: E. Meher Abhinav, Gopalakrishnan Chandrasekaran, S.V. Kasmir Raja

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## ACCEPTED MANUSCRIPT

# Strain and Deformations Engineered Germanene Bilayer Double Gate-Field Effect Transistor by First Principles

E Meher Abhinav<sup>1</sup>, Gopalakrishnan Chandrasekaran<sup>1</sup>\* and S. V. Kasmir Raja<sup>2</sup>

<sup>1</sup>Nanotechnology Research Centre, SRM University, kattankulathur, Kancheepuram District - 603203 Tamil Nadu, India.

<sup>2</sup>Directorate of Research and Virtual Education, SRM University, Kattankulathur, India.

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